Oral presentation | 15. Crystal Engineering | 15.4 III-V-group nitride crystals

[19p-B5-1~22] 15.4 III-V-group nitride crystals
Thu. Sep 19, 2013 1:00 PM - 7:15 PM  B5 (TC2 2F-201)
△: Young Scientist Oral Presentation Award Applied
▲: English Presentation
▼: Both Award Applied and English Presentation

1:00 PM - 1:30 PM

[19p-B5-1][JSAP Paper Award Speech](30 min.) Preparation of a Freestanding AlN Substrate from a Thick AlN Layer Grown by Hydride Vapor Phase Epitaxy on a Bulk AlN Substrate Prepared by Physical Vapor Transport
Yoshinao Kumagai¹, Yuki Kubota², Toru Nagashima¹,², Toru Kinoshita², Rafael Dalmau³, Raoul Schlesser³, Baxter Moody³, Jinqiao Xie³, Hisashi Murakami¹, Akinori Koukitu¹, Zlatko Sitar³,⁴ (TUAT¹, TOKUYAMA², HexaTech³, NC State Univ.⁴)